



60V 175°C P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
-60V	$33m\Omega @ V_{GS} = -10V$	-35A
	40mΩ @ V _{GS} = -4.5V	-32A

Description and Applications

This MOSFET has been designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

Features

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- Low On-Resistance
- Low Input Capacitance
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

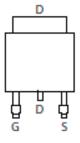
Mechanical Data

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 ⁽³⁾
- Terminal Connections: See Diagram
- Weight: 0.33 grams (Approximate)

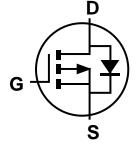
TO252 (DPAK)



Top View



Pin Out Top View



Equivalent Circuit

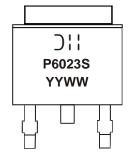
Ordering Information (Note 5)

Part Number	Case	Packaging
DMPH6023SK3Q-13	TO252 (DPAK)	2,500/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



| | =Manufacturer's Marking | P6023S = Product Type Marking Code | YYWW = Date Code Marking | YY = Last Two Digits of Year (ex: 16 = 2016) | WW = Week Code (01 to 53)



Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V _{DSS}	-60	V		
Gate-Source Voltage	V _{GSS}	±20	V		
Continuous Durin Compant (Nata 7) V	Steady State	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	I _D	-35 -27	А
Continuous Drain Current (Note 7) V _{GS} = -10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	-7.3 -6.1	А
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%	I _{DM}	-60	Α		
Maximum Continuous Body Diode Forward Current (I _S	-2.2	Α		
Avalanche Current (Note 8) L = 0.1mH	I _{AS}	-35	Α		
Avalanche Energy (Note 8) L = 0.1mH	E _{AS}	60	mJ		

Thermal Characteristics

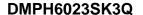
Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 6)		P_{D}	2.0	W
Thermal Resistance, Junction to Ambient (Note 6) Steady State		$R_{\theta JA}$	80	°C/W
Total Power Dissipation (Note 7)	P_D	3.2	W	
Thermal Resistance, Junction to Ambient (Note 7) Steady State		$R_{\theta JA}$	41	°C/W
Thermal Resistance, Junction to Case	R ₀ JC	1.6	C/VV	
Operating and Storage Temperature Range		$T_{J,}T_{STG}$	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

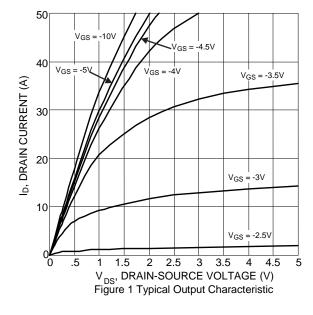
Observatoristis	0	NA:	T	NA	1124	To at O and distant	
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)						_	
Drain-Source Breakdown Voltage	BV _{DSS}	-60	_	_	V	$V_{GS} = 0V, I_{D} = -250\mu A$	
Zero Gate Voltage Drain Current , T _J = +25°C			_	-1	μΑ	$V_{DS} = -60V, V_{GS} = 0V$	
Gate-Source Leakage	IGSS	_		±100	nA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V _{GS(TH)}	-1.0	_	-3.0	V	$V_{DS} = V_{GS}$, $I_D = -250\mu A$	
Static Drain-Source On-Resistance	Paggara	_	_	33	mΩ	$V_{GS} = -10V, I_D = -10A$	
Static Dialii-Source Off-Resistance	R _{DS(ON)}	_	_	40	11122	$V_{GS} = -4.5V, I_D = -8A$	
Diode Forward Voltage	V_{SD}	_	-0.7	-1.2	٧	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C _{iss}	-	2,569	_	рF	\\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	
Output Capacitance	Coss	1	179		рF	$V_{DS} = -30V, V_{GS} = 0V,$ - f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	-	143		рF	T = 1.0IVII IZ	
Gate Resistance	R_g	-	5	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = -4.5V)	Q_g	-	26.5		nC		
Total Gate Charge (V _{GS} = -10V)	Q_{g}	1	53.1		nC	\/ 20\/ I- 5A	
Gate-Source Charge	Q_{gs}	1	7.1		nC	$V_{DS} = -30V, I_{D} = -5A$	
Gate-Drain Charge	Q_{gd}	1	12.6		nC	1	
Turn-On Delay Time	t _{D(ON)}	_	6	_	ns		
Turn-On Rise Time	t _R	_	7.1	_	ns	$V_{GS} = -10V, V_{DS} = -30V,$ $R_{G} = 3\Omega, I_{D} = -5A$	
Turn-Off Delay Time	t _{D(OFF)}	_	110	_	ns		
Turn-Off Fall Time	t _F	_	62	_	ns		
Body Diode Reverse Recovery Time	t _{RR}	_	20	_	ns		
Body Diode Reverse Recovery Charge	Q _{RR}	_	14	4 — nC IF = -5A, di/dt = 100A		$I_F = -5A$, di/dt = 100A/ μ s	

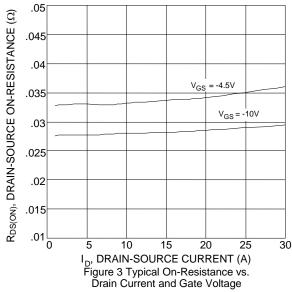
Notes:

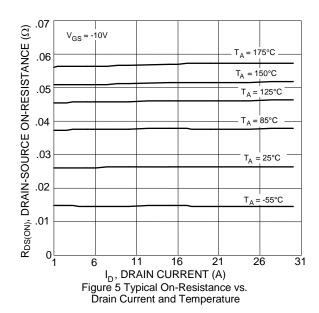
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
- 7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.
- 8. I $_{AS}$ and E $_{AS}$ ratings are based on low frequency and duty cycles to keep T $_{J}$ = +25°C.
- 9. Short duration pulse test used to minimize self-heating effect.
- 10. Guaranteed by design. Not subject to product testing.

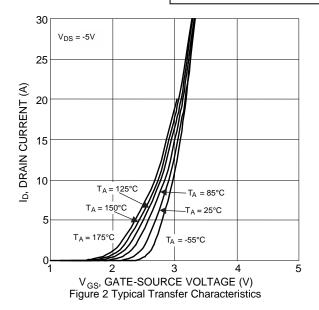


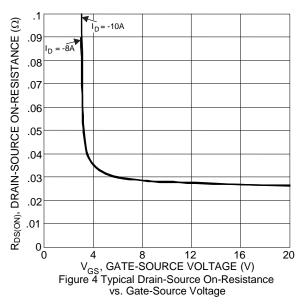


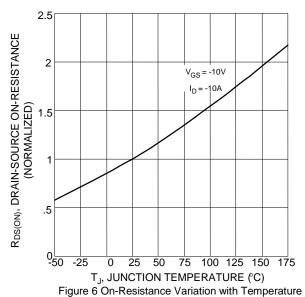




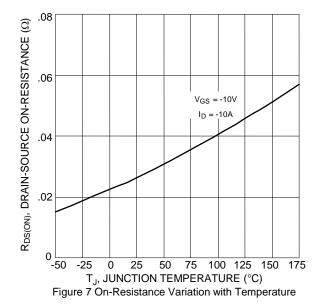


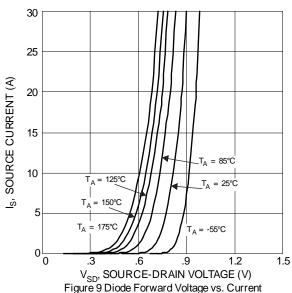


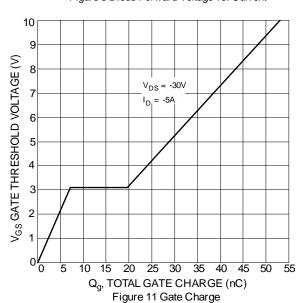












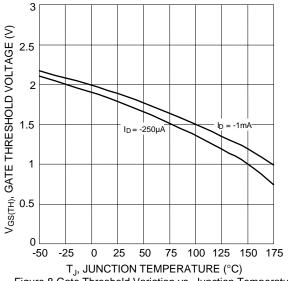


Figure 8 Gate Threshold Variation vs. Junction Temperature

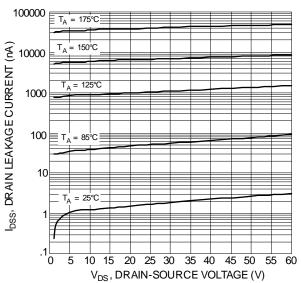
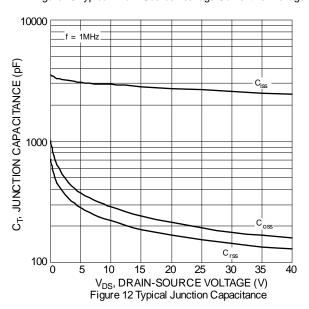
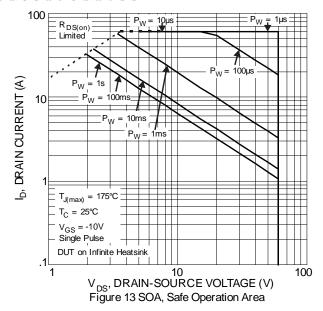
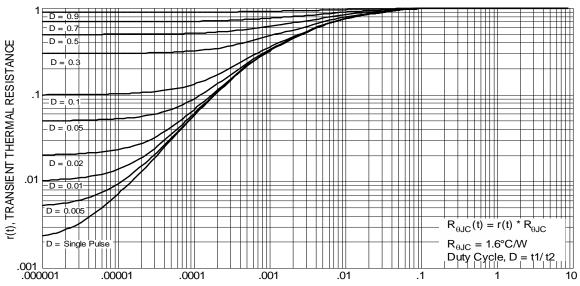


Figure 10 Typical Drain-Source Leakage Current vs. Voltage









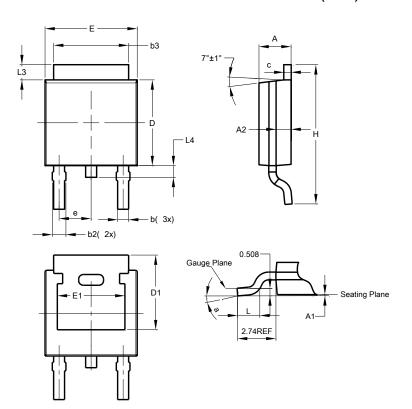
t1, PULSE DURATION TIME (sec) Figure 14 Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)

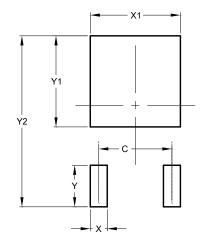


TO252 (DPAK)					
Dim	Min	Max	́Тур		
Α	2.19	2.39	2.29		
A 1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
С	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	-		
е	1	-	2.286		
Е	6.45	6.70	6.58		
E1	4.32	-	-		
H	9.40	10.41	9.91		
L	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)			
С	4.572			
Х	1.060			
X1	5.632			
Υ	2.600			
Y1	5.700			
Y2	10.700			



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